

P-Channel MOSFET

Description

The PPMDP03R18L uses trench technology to provide excellent $R_{\rm DS(ON)}$ low gate charge. This device is suitable for power management and high efficiency applications at high switching frequencies applications.

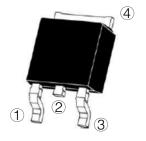
MOSFET Product Summary				
V _{DS} (V)	$V_{DS}(V)$ $R_{DS(on)}(m\Omega)(Typ)$			
-30	11.2 @ V _{GS} = -10V	-43		
	16.7 @ V _{GS} = -4.5V	-43		

Feature

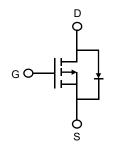
- > High Power and current handing capability
- > Lead free product is acquired
- > Surface Mount Package

Applications

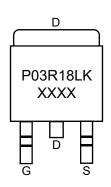
- > PWM applications
- Load Switch
- Power Management
- > DC-DC Converters
- Wireless Chargers



TO-252 (Top View)



Circuit Diagram



Marking (Top View)

Absolute maximum rating@25°C

Rating	Symbol	Value	Units	
Drain-Source Voltage	V _{DS}	-30	V	
Gate-Source Voltage		V _{GS}	±20	V
Drain Current-Continuous ¹⁾	T _C =25°C	1	-43	Α
	T _C =100°C	- I _D	-27.4	A
Pulsed Drain Current ²⁾	I _{DM}	-160	А	
Total Power Dissipation ³⁾	P _D	33.8	W	
Avalanche Current ⁴⁾	I _{AS}	-21	Α	
Avalanche Energy ⁴⁾	anche Energy ⁴⁾		114	mJ
Thermal Resistance , Junction-to-Case ⁵⁾	mal Resistance , Junction-to-Case ⁵⁾		3.0	°C/W
Thermal Resistance , Junction-to-Ambient ⁵⁾		$R_{\theta JA}$	37	°C/W
Junction and Storage Temperature Range		$T_{J,}T_{STG}$	-55~+150	°C

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units	
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	$V_{GS} = 0V, I_{D} = -250\mu A$	-30	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -30V, V_{GS} = 0V$	-	-	-1.0	μA	
Gate-Body Leakage Current	I _{GSS}	$V_{GS} = \pm 20 V, V_{DS} = 0 V$	ı	-	±100	nA	
On Characteristics							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-1.0	-1.6	-2.5	V	
Drain-Source On-State Resistance	В	$V_{GS} = -10V, I_{D} = -20A$	-	11.2	15		
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = -4.5V, I_{D} = -15A$	-	16.7	22	mΩ	
Dynamic Characteristics ⁶⁾							
Input Capacitance	C _{lss}		-	1400	-	pF	
Output Capacitance	C _{oss}	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	-	147	-		
Reverse Transfer Capacitance	C _{rss}		-	131	-		
Switching Characteristics ⁶⁾							
Turn-on Delay Time	t _{d(on)}		-	7.0	-		
Turn-on Rise Time	t _r	V _{DS} = -15V, V _{GS} = -10V,	-	55	-		
Turn-Off Delay Time	t _{d(off)}	$R_{G} = 2.5\Omega, I_{D} = -15A$	-	58	-	ns	
Turn-Off Fall Time	t _f		-	81	-		
Total Gate Charge	Q_g		-	26.3	-		
Gate-Source Charge	Q_{gs}	$V_{DS} = -15V, V_{GS} = -10V,$ $I_{D} = -15A$	-	3.9	-	nC	
Gate-Drain Charge	Q_{gd}		-	5.2	-		
Drain-Source Diode Characteristics							
Diode Forward Voltage	V _{SD}	$V_{GS} = 0V, I_{S} = -20A$	-	-0.8	-1.2	V	

Notes

Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.

Repetitive Rating: Pulse width limited by maximum junction temperature(T_{J Max}=150°C).

Pulse Test: Pulse Width ≤ 10µs, Duty Cycle ≤ 1%.

^{4.} This single-pulse measurement was taken under the following condition [L=0.5mH,V_{GS}=-10V,V_{DS}=-30V]while it's value is limited by T_{J Max}=150°C.

^{5.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.

^{6.} Guaranteed by design, not subject to production.

Typical Characteristics

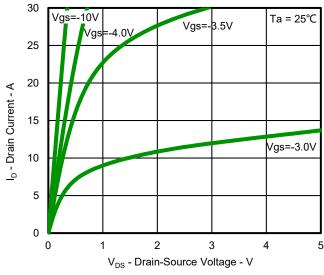


Fig.1 Output Characteristics

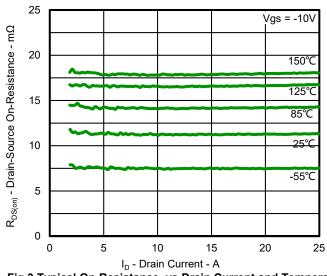


Fig.3 Typical On-Resistance vs Drain Current and Temperature

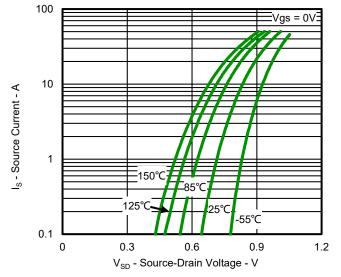


Fig.5 Diode Forward Voltage vs. Current

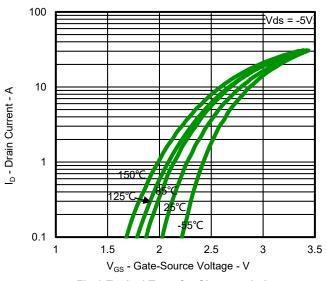


Fig.2 Typical Transfer Characteristic

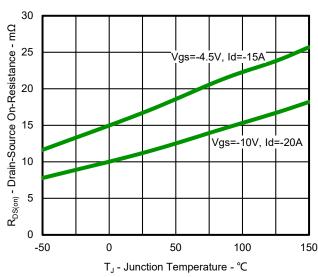


Fig.4 On-Resistance Variation with Temperature

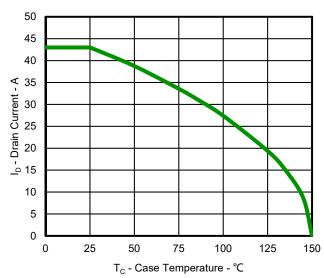


Fig.6 Maximum Drain Current vs. Case Temperature

P-Channel MOSFET

0.001

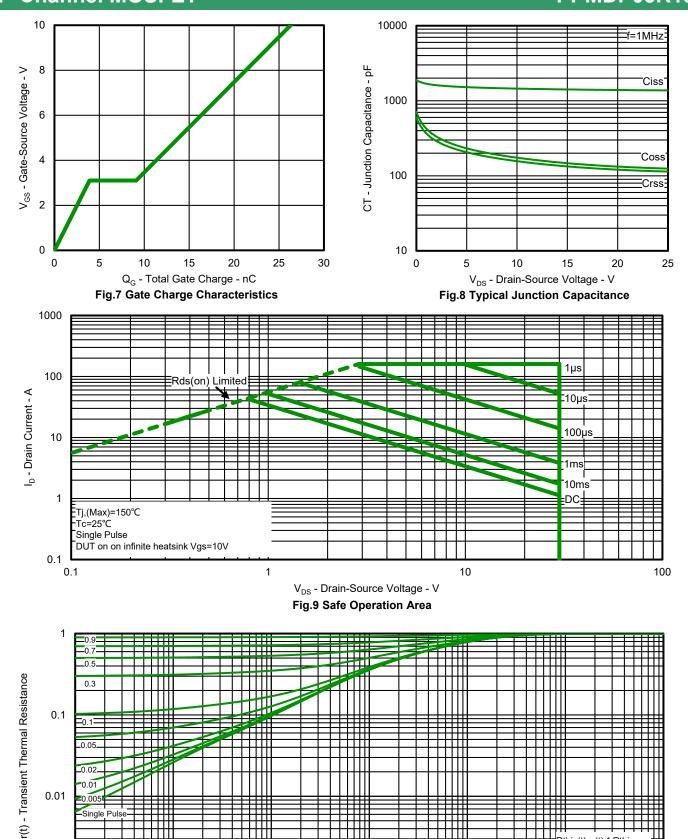
0.000001

0.00001

PPMDP03R18L

Rthjc(t)=r(t) * Rthjc Rthjc=3.05°C/W Duty Cycle, D=t1 / t2

0.1



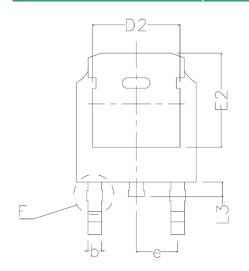
t1 - Pulse Duration Time - sec Fig.10 Transient Thermal Resistance

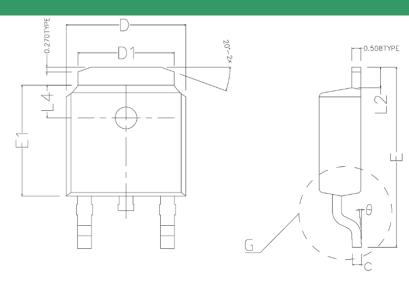
0.001

0.01

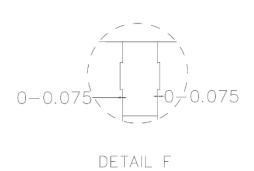
0.0001

Product Dimension (TO-252)

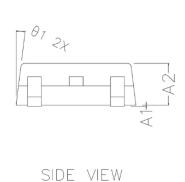




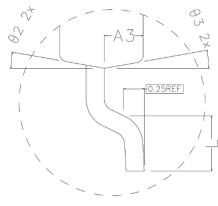
BOTTOM VIEW



TOP VIEW



SIDE VIEW



DETAIL G

Dim	Millim	Millimeters		hes	Dim	Millim	neters	Inc	hes
Dilli	Min	Max	Min	Max	Dim	Min	Max	Min	Max
A1	0.03	0.13	0.001	0.005	E2	5.14 Ref.		0.202 Ref.	
A2	2.20	2.40	0.087	0.094	е	2.286	3 Тур.	0.090	Тур.
A3	0.96	1.06	0.038	0.042	L	1.40	1.60	0.055	0.063
b	0.64	0.74	0.025	0.029	L2	1.00 Ref.		0.039 Ref.	
С	0.46	0.55	0.018	0.022	L3	0.80	Ref.	0.031	Ref.
D	6.50	6.70	0.256	0.264	L4	1.80 Ref.		0.071 Ref.	
D1	5.334	Ref.	0.210	Ref.	θ	0°	8°	0°	8°
D2	4.83	Ref.	0.190	Ref.	θ1	7° 7	Гур.	7° ٦	Гур.
Е	9.77	10.17	0.385	0.400	θ2	7° 7	Гур.	7° ∃	Гур.
E1	6.00	6.20	0.236	0.244	θ3	7° Тур.		7 ° ∃	Гур.

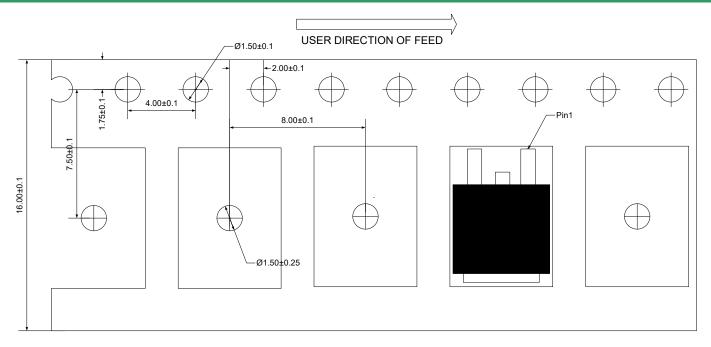
P-Channel MOSFET

PPMDP03R18L

Ordering Information

Package	Reel	Shipping
TO-252	13"	2500 / Tape & Reel

Load With Information



Unit:mm

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